

CSD15380F3 20-V N-Channel FemtoFET™ MOSFET

1 Features

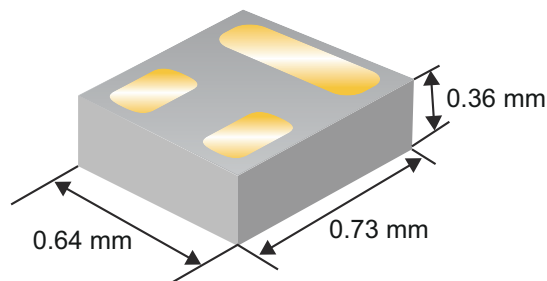
- Ultra-low C_{iss} and C_{oss}
- Ultra-low Q_g and Q_{gd}
- Ultra-small footprint
 - 0.73 mm × 0.64 mm
- Ultra-low profile
 - 0.36-mm max height
- Integrated ESD protection diode
 - Rated > 4-kV HBM
 - Rated > 2-kV CDM
- Lead and halogen free
- RoHS compliant

2 Applications

- Optimized for load switch applications
- Optimized for general purpose switching applications
- Battery applications
- Handheld and mobile applications

3 Description

This 20-V, 990-mΩ, N-Channel FemtoFET™ MOSFET is designed and optimized to minimize the footprint in many handheld and mobile applications. Ultra-low capacitance improves switching speeds. When used in data line applications, the low capacitance minimizes noise coupling. This technology is capable of replacing standard small signal MOSFETs while providing a substantial reduction in footprint size.



Typical Part Dimensions

Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	20	V
Q_g	Gate Charge Total (4.5 V)	0.216	nC
Q_{gd}	Gate Charge Gate-to-Drain	0.027	nC
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 2.5\text{ V}$	2220
		$V_{GS} = 4.5\text{ V}$	1170
		$V_{GS} = 8\text{ V}$	990
$V_{GS(th)}$	Threshold Voltage	1.1	V

Device Information⁽¹⁾

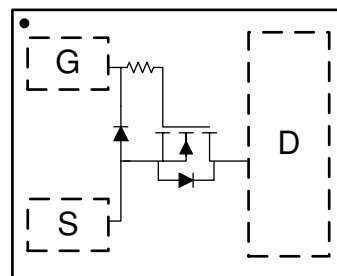
DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD15380F3	3000	7-Inch Reel	Femto	Tape and Reel
CSD15380F3T	250		0.73-mm × 0.64-mm Land Grid Array (LGA)	

- (1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ (unless otherwise stated)		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	20	V
V_{GS}	Gate-to-Source Voltage	10	V
I_D	Continuous Drain Current ⁽¹⁾	0.9	A
	Continuous Drain Current ⁽²⁾	0.5	
I_{DM}	Pulsed Drain Current ⁽³⁾	1.6	A
P_D	Power Dissipation ⁽¹⁾	1.4	W
	Power Dissipation ⁽²⁾	0.5	
$V_{(ESD)}$	Human-Body Model (HBM)	4	kV
	Charged-Device Model (CDM)	2	
T_J, T_{stg}	Operating Junction and Storage Temperature	–55 to 150	°C

- (1) Typical $R_{\theta JA} = 90^\circ\text{C/W}$ on 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu pad on a 0.06-in (1.52-mm) thick FR4 PCB
- (2) Typical $R_{\theta JA} = 255^\circ\text{C/W}$ on min Cu board
- (3) Pulse duration ≤ 100 μs, duty cycle ≤ 1%.



Top View



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (July 2017) to Revision B (February 2022)	Page
• Changed ultra-low profile bullet from 0.35 mm to 0.36 mm in height.....	1
• Updated ultra-low profile image height from 0.35 mm to 0.36 mm.....	1
• Changed ultra-low profile image height from 0.35 mm to 0.36 mm.....	7
• Added FemtoFET Surface Mount Guide note.....	8

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• Updated ultra-low profile image height from 0.35 mm to 0.36 mm.....	1
• Changed ultra-low profile image height from 0.35 mm to 0.36 mm.....	7
• Added FemtoFET Surface Mount Guide note.....	8

5 Specifications

5.1 Electrical Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV _{DSS}	Drain-to-source voltage	V _{GS} = 0 V, I _{DS} = 250 μA	20			V
I _{DSS}	Drain-to-Source leakage current	V _{GS} = 0 V, V _{DS} = 16 V	50			nA
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 10 V	25			nA
V _{GS(th)}	Gate-to-source threshold voltage	V _{DS} = V _{GS} , I _{DS} = 2.5 μA	0.85	1.10	1.35	V
R _{DS(on)}	Drain-to-source on-resistance	V _{GS} = 2.5 V, I _{DS} = 0.1 A	2220		4000	mΩ
		V _{GS} = 4.5 V, I _{DS} = 0.1 A	1170		1460	
		V _{GS} = 8 V, I _{DS} = 0.1 A	990		1190	
g _{fs}	Transconductance	V _{DS} = 2 V, I _{DS} = 0.1 A	0.64			S
DYNAMIC CHARACTERISTICS						
C _{iss}	Input capacitance	V _{GS} = 0 V, V _{DS} = 10 V, f = 1 MHz	8.1		10.5	pF
C _{oss}	Output capacitance		5.9		7.7	pF
C _{rss}	Reverse transfer capacitance		0.13		0.17	pF
R _G	Series gate resistance		9.6			Ω
Q _g	Gate charge total (4.5 V)	V _{DS} = 10 V, I _{DS} = 0.1 A	0.216		0.281	nC
Q _{gd}	Gate charge gate-to-drain		0.027			nC
Q _{gs}	Gate charge gate-to-source		0.077			nC
Q _{g(th)}	Gate charge at V _{th}		0.048			nC
t _{d(on)}	Turnon delay time	V _{DS} = 10 V, V _{GS} = 4.5 V, I _{DS} = 0.1 A, R _G = 0 Ω	3			ns
t _r	Rise time		1			ns
t _{d(off)}	Turnoff delay time		7			ns
t _f	Fall time		7			ns
DIODE CHARACTERISTICS						
V _{SD}	Diode forward voltage	I _{SD} = 0.1 A, V _{GS} = 0 V	0.85		1	V

5.2 Thermal Information

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

THERMAL METRIC		TYPICAL VALUES	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾	90	$^\circ\text{C/W}$
	Junction-to-ambient thermal resistance ⁽²⁾	255	

- (1) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.
 (2) Device mounted on FR4 material with minimum Cu mounting area.

5.3 Typical MOSFET Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

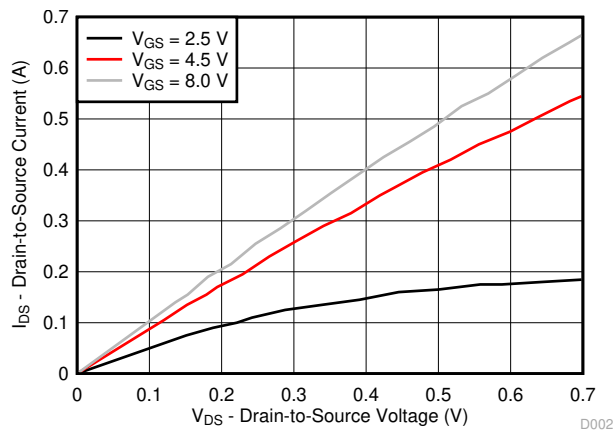


Figure 5-1. Saturation Characteristics

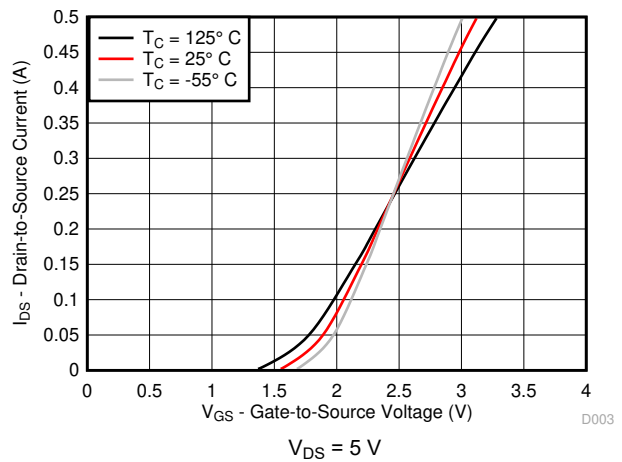


Figure 5-2. Transfer Characteristics

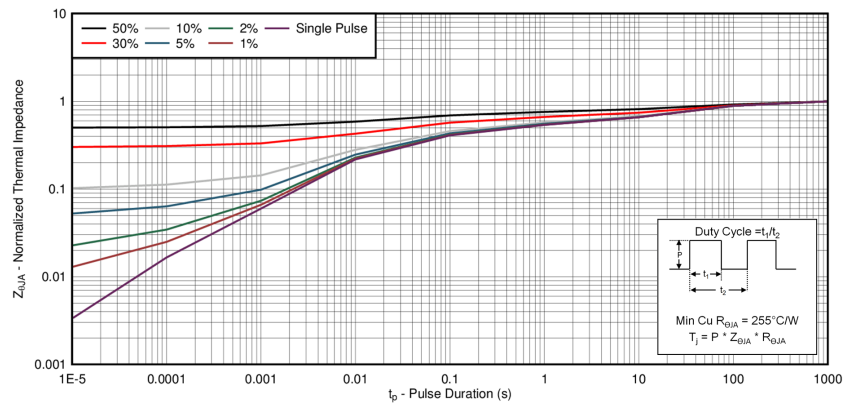


Figure 5-3. Transient Thermal Impedance

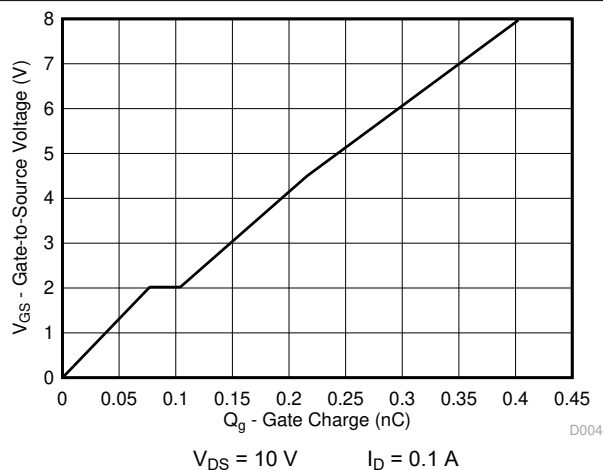


Figure 5-4. Gate Charge

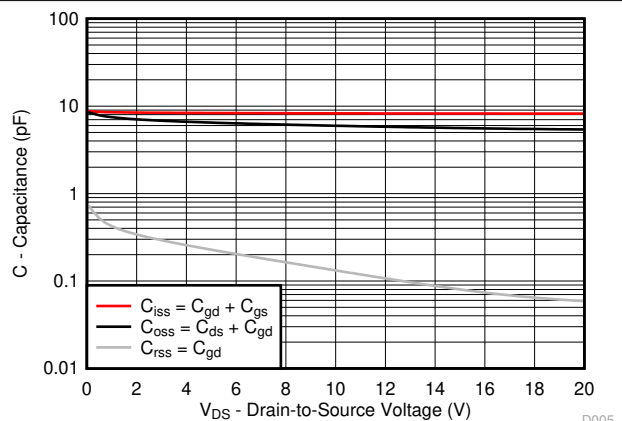


Figure 5-5. Capacitance

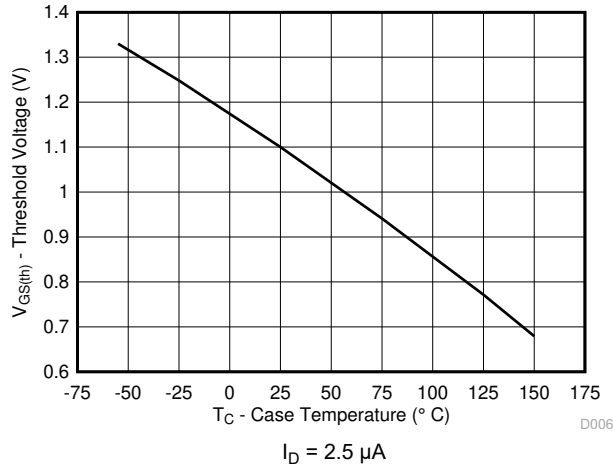


Figure 5-6. Threshold Voltage vs Temperature

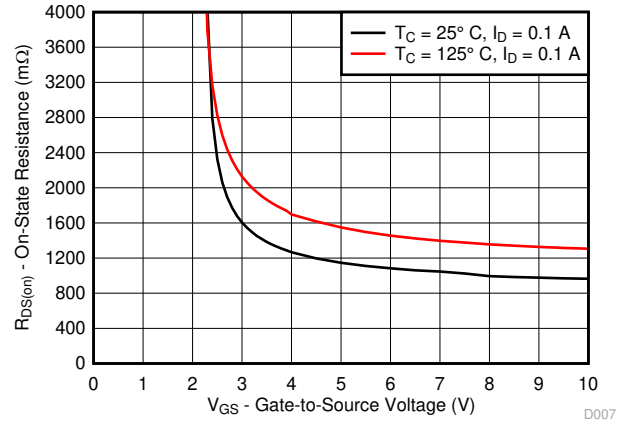


Figure 5-7. On-State Resistance vs Gate-to-Source Voltage

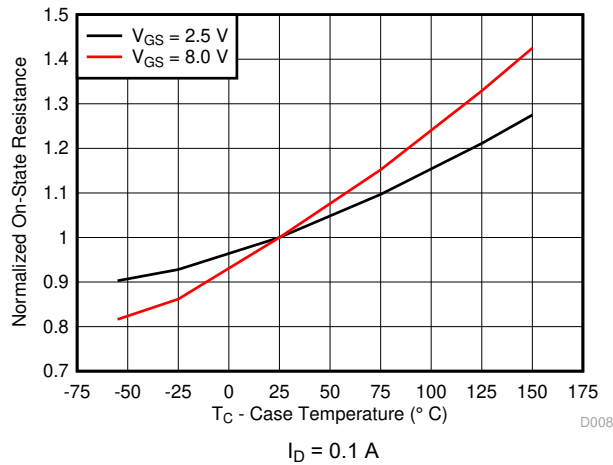


Figure 5-8. Normalized On-State Resistance vs Temperature

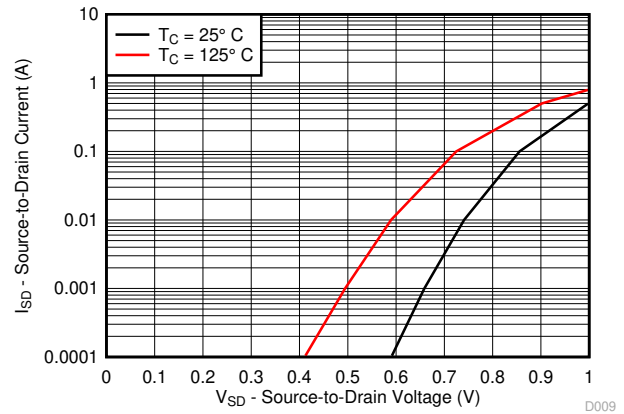


Figure 5-9. Typical Diode Forward Voltage

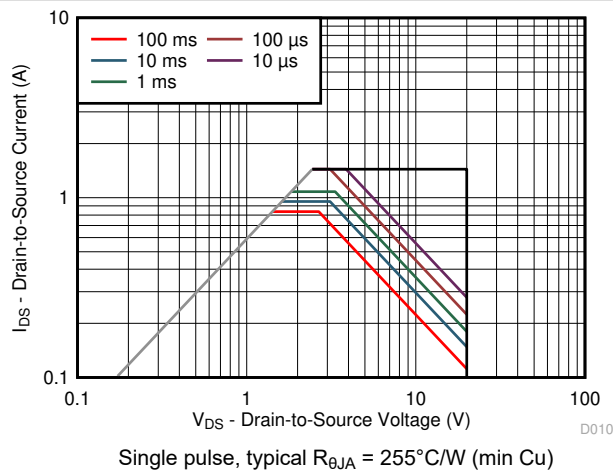


Figure 5-10. Maximum Safe Operating Area

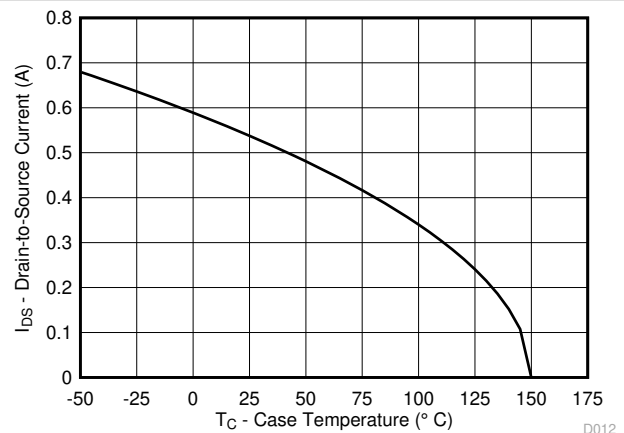


Figure 5-11. Maximum Drain Current vs Temperature

6 Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Trademarks

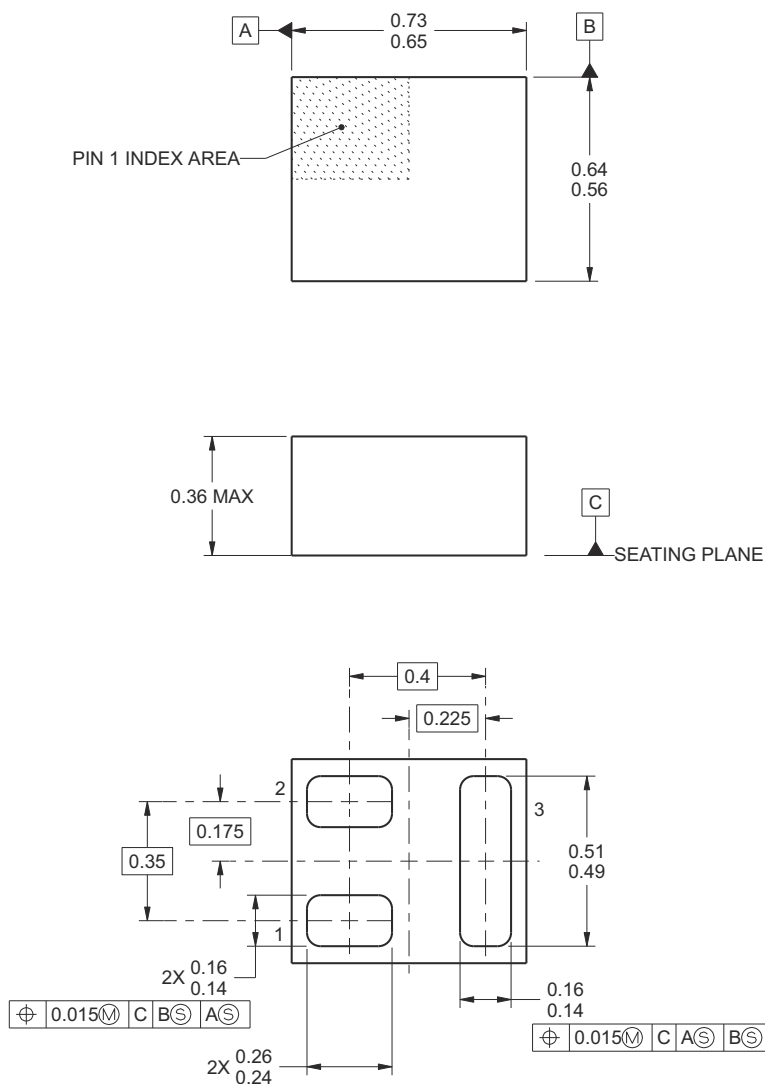
FemtoFET™ is a trademark of Texas Instruments.

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7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Mechanical Dimensions

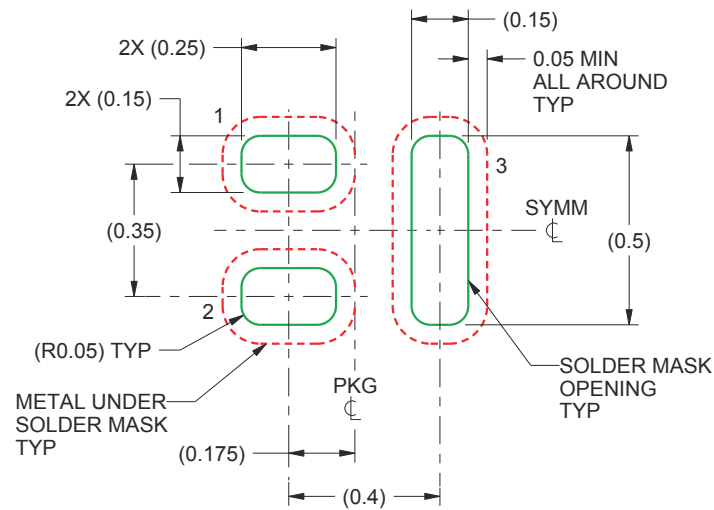


- A. All linear dimensions are in millimeters (dimensions and tolerancing per ASME Y14.5M-1994).
- B. This drawing is subject to change without notice.
- C. This package is a lead-free solder land design.

Table 7-1. Pin Configuration

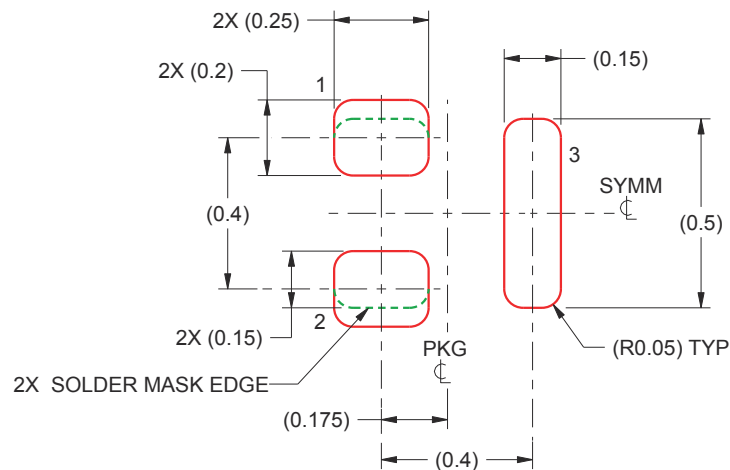
POSITION	DESIGNATION
Pin 1	Gate
Pin 2	Source
Pin 3	Drain

7.2 Recommended Minimum PCB Layout



- A. All dimensions are in millimeters.
- B. For more information, see [FemtoFET Surface Mount Guide](#) (SLRA003D).

7.3 Recommended Stencil Pattern



- A. All dimensions are in millimeters.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD15380F3	Active	Production	PICOSTAR (YJM) 3	3000 LARGE T&R	Yes	NIAU	Level-1-260C-UNLIM	-55 to 150	6
CSD15380F3.B	Active	Production	PICOSTAR (YJM) 3	3000 LARGE T&R	Yes	NIAU	Level-1-260C-UNLIM	-55 to 150	6
CSD15380F3T	Active	Production	PICOSTAR (YJM) 3	250 SMALL T&R	Yes	NIAU	Level-1-260C-UNLIM	-55 to 150	6
CSD15380F3T.B	Active	Production	PICOSTAR (YJM) 3	250 SMALL T&R	Yes	NIAU	Level-1-260C-UNLIM	-55 to 150	6

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

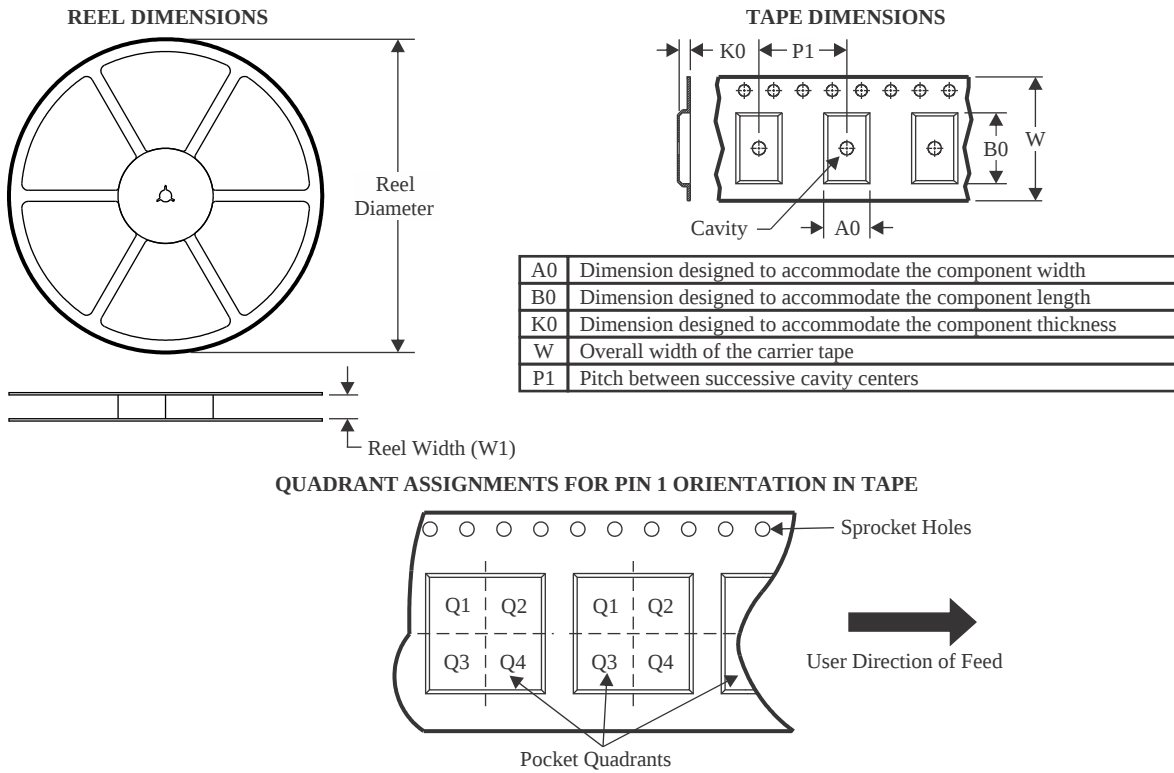
⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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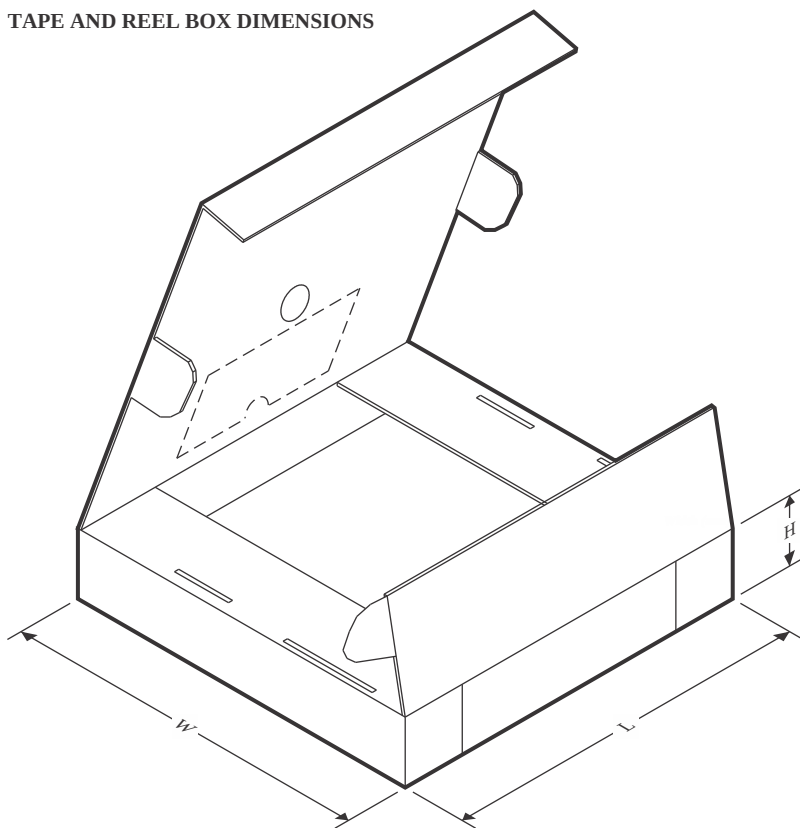
TAPE AND REEL INFORMATION



*All dimensions are nominal

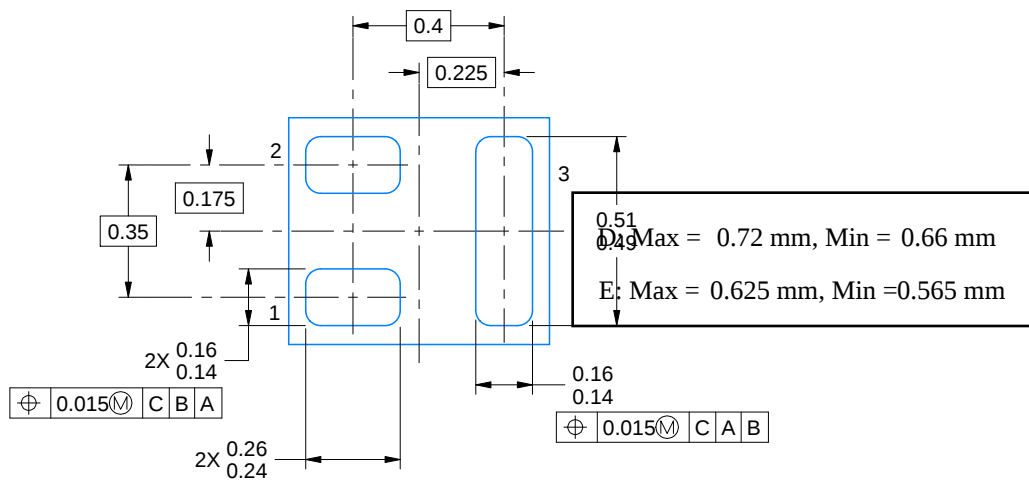
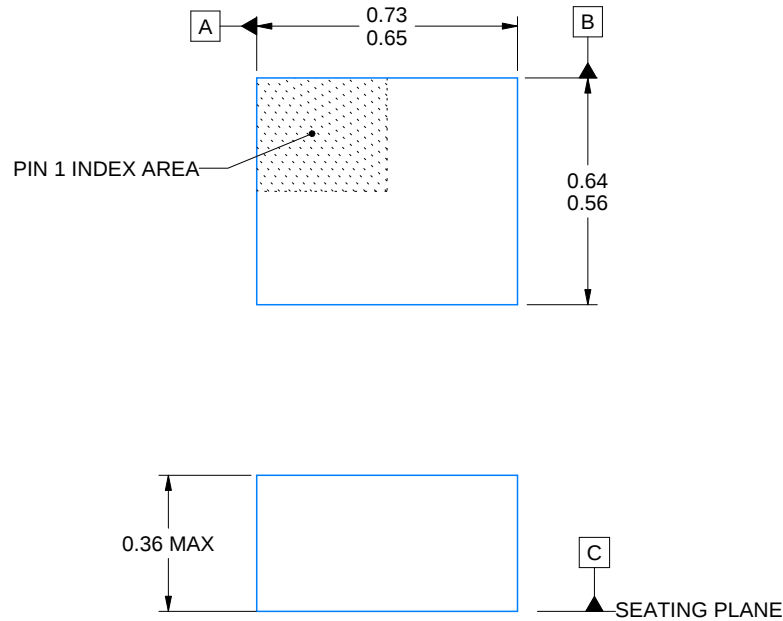
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD15380F3	PICOSTAR	YJM	3	3000	180.0	8.4	1.94	0.79	0.44	4.0	8.0	Q2
CSD15380F3T	PICOSTAR	YJM	3	250	180.0	8.4	1.94	0.79	0.44	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD15380F3	PICOSTAR	YJM	3	3000	182.0	182.0	20.0
CSD15380F3T	PICOSTAR	YJM	3	250	182.0	182.0	20.0

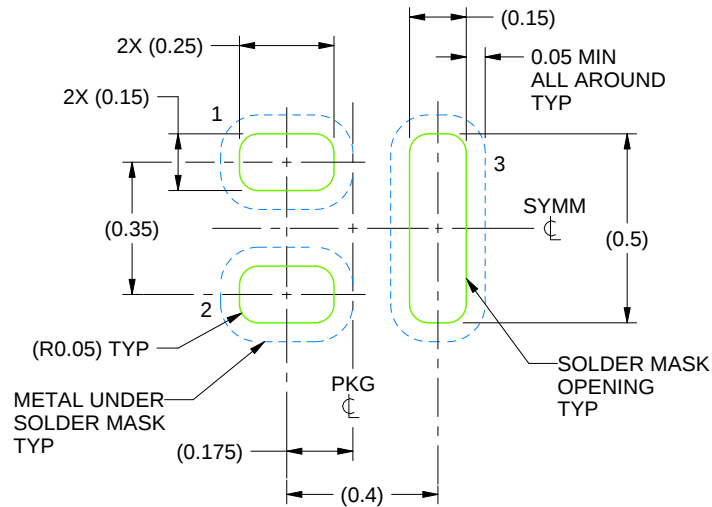


4222304/B 03/2022

NOTES:

PicoStar is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M
2. This drawing is subject to change without notice.
3. This package is a Pb-free bump design. Bump finish may vary. To determine the exact finish, refer to the device datasheet or contact a local TI representative.

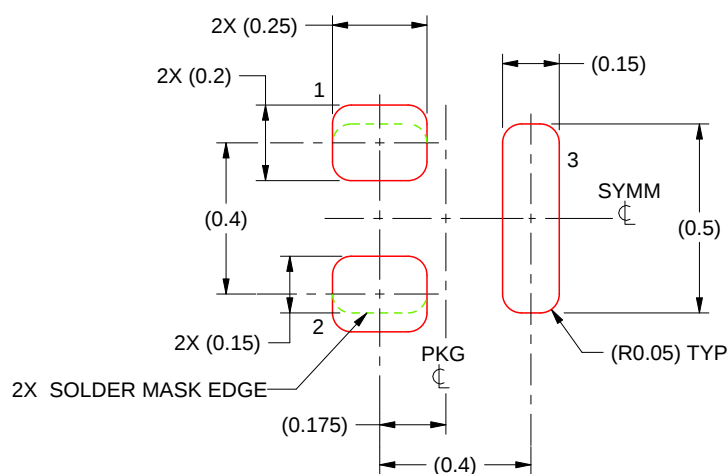


LAND PATTERN EXAMPLE
SOLDER MASK DEFINED
SCALE:50X

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NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slue271).



SOLDER PASTE EXAMPLE
 BASED ON 0.075 - 0.1 mm THICK STENCIL
 SCALE:50X

4222304/B 03/2022

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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